

General Description

The EC95808 series are highly accurate, ultra-low current consumption voltage detectors, developed by CMOS process. Two output forms N-channel open-drain and CMOS output are available. The device is ideal for battery powered portable devices which require low current consumption.

The EC95808 consists of a comparator, a voltage reference unit, a resistor divider, an output driver, and a hysteresis circuit. The detection voltage is fixed internally with $\pm 2.0\%$ accuracy by advanced trimming technology.

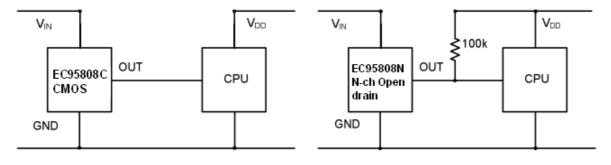
The devices are available in SOT23-3L,SC82-4L and SC70-3L packages.

Features

- Ultra-Low Quiescent Current 1.0 µA (Typ.)
- High Accuracy of Detection Voltage ±2%
- Hysteresis Width 5% VDET (Typ.)
- Detection Voltage 1.6V to 6.0V (0.1V Step)
- Operating Voltage Range 1.5V to 6.0V
- N-ch Open Drain and CMOS Output
- SOT23-3L, SC82-4Land SC70-3L Packages
- RoHS Compliant and 100% Lead (Pb)-Free and Green (Halogen Free with Commercial Standard)

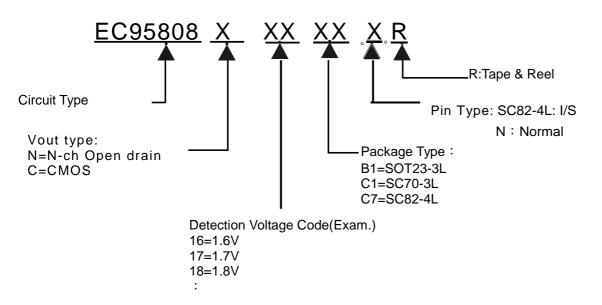
Applications

- Microprocessor Reset Circuitry
- Memory Battery Back-up Circuits
- Power-on Reset Circuits
- Power Failure Detection
- System Battery Life and Charge Voltage Monitors



Typical Application Circuit

Ordering Information

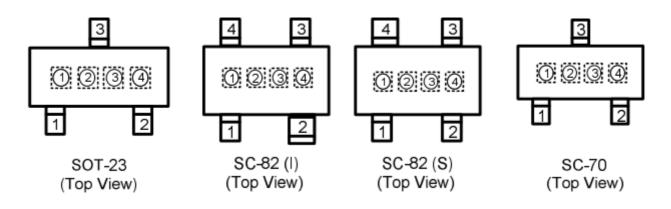




Pin Description

Part NO.	Part NO.	Pin	Symbol	Pin Description
<u>3</u>		1	V _{OUT}	Regulator Output Pin.
(Top View)	EC95808NXXB1NR EC95808CXXB1NR	2	GND	Ground Pin.
SOT23-3L		3	V _{IN}	Regulator Input Pin.
4 3		1	Vout	Regulator Output Pin.
(Top View)	EC95808NXXC7IR EC95808CXXC7IR -	2	V _{IN}	Regulator Input Pin.
1 2		3	NC	No Connect
SC82-4L(Pin Typel)		4	GND	Ground Pin.
4 3		1	V _{OUT}	Regulator Output Pin.
(Top View)	EC95808NXXC7SR	2	V _{IN}	Regulator Input Pin.
	EC95808CXXC7SR	3	NC	No Connect
SC82-4L(Pin Type S)		4	GND	Ground Pin.
3		1	GND	Ground Pin.
(Top View)	EC95808NXXC1NR EC95808CXXC1NR	2	Vout	Regulator Output Pin.
SC70-3L		3	V _{IN}	Regulator Input Pin.

Marking Information





(1) Represents Products Series(See Note1)

Mark	Vout Type	Voltage(V)	Mark	Vout Type	Voltage(V)
A	CMOS	0.X	Н	N-ch	0.X
В	CMOS	1.X	J	N-ch	1.X
С	CMOS	2.X	К	N-ch	2.X
D	CMOS	3.X	L	N-ch	3.X
E	CMOS	4.X	М	N-ch	4.X
F	CMOS	5.X	Ν	N-ch	5.X
G	CMOS	6.X	Р	N-ch	6.X

(2) Represents decimal number of detect voltage(See Note 2)

Mark	Voltage(V)	Mark	Voltage(V)
0	X.0	5	X.5
1	X.1	6	X.6
2	X.2	7	X.7
3	X.3	8	X.8
4	X.4	9	X.9

(3) (4) Represents Production Date Code

Note :

 * There are two under-lines on 4 th & 5 th digit for Green package.

 * There are no under-lines on 4 th & 5 th digit for Pb-Free package.

Absolute Maximum Rating

Parameter		Symbol	Ratings	Units
Input Voltage V _{IN}	to GND	V _{IN}	6.0	V
Output Voltage,	CMOS	V _{OUT}	GND~V _{IN} +0.3V	V
Output Voltage	, N-ch		GND~6V	
Output Curr	Output Current		50	mA
Junction Tempe	Junction Temperature		+155	C
Power Dissipation	SOT23-3L	P _D	310	mW
	SC82-4L		250	
	SC70-3L		250	
Operating Ambient Temperature		T _{OPR}	-40 ~ +85	C
Storage Temperature		T _{STG}	-55 ~ +150	C
Lead Temperature (sold	ering, 10sec)		+260	C

Note :

* The power dissipation values are based on the condition that junction temperature T_J and ambient temperature T_A difference is 100°C.

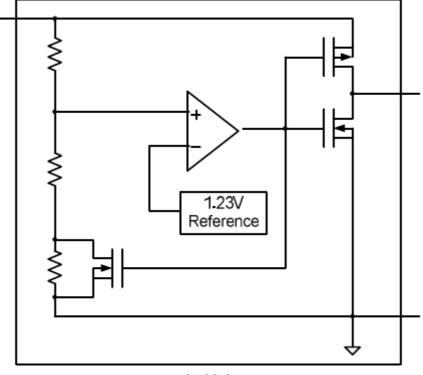
* Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and function operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum -rated conditions for extended periods may affect device reliability.

Electrical Characteristics(T_A=25°C, unless otherwise noted.)

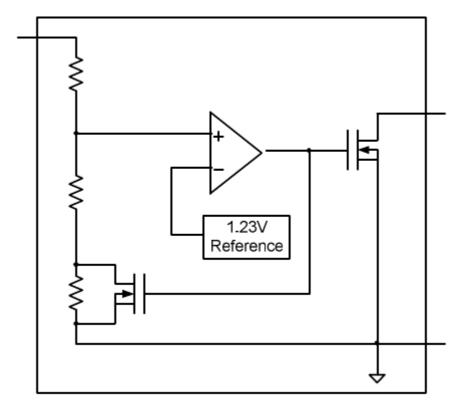
Symbol	Parameter	Test	Conditions	Min	Тур	Max	Unit
V _{IN}	Operating Voltage			1.5		6.0	V
V _{DET}	Detection Voltage			V _{DET} * 0.98	V _{det}	V _{DET} * 1.02	V
V _{HYS}	Hysteresis Width				V _{DET} * 0.05	V _{DET} * 0.08	V
Ι _Q	Quiescent Current	V _{IN} =5V			1.0	3.0	μA
		N-ch	V _{IN} =2V	3	7		
I _{OUT}	Output Current	Output	V _{IN} =3V	5	10		mA
			V _{IN} =5V	7	13		
I _{LEAK}	Leakage Current	N-ch, $V_{IN}=V_O$	_{UT} =5V			0.1	μΑ
T _c	Temperature Coefficient	-40℃ <t <sub="">A< +</t>	85°C		100	350	ppm/ ℃
	Response Time					200	μS



Function Block Diagram



CMOS Output



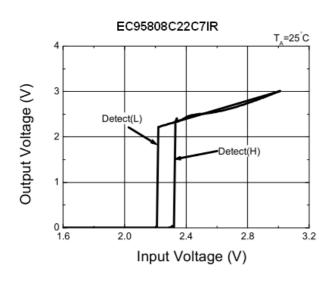
N-ch Open drain Output



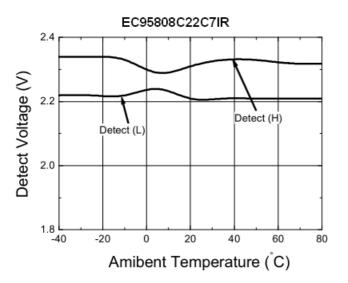
Typical Operating Characteristics

(EC95808C22C7IR tested, T_A=+25 $^{\circ}$ C, unless otherwise noted.)

(1) Output Voltage vs. Input Voltage

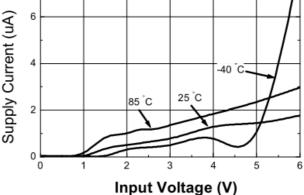


(3) Detect Voltage v.s Amibent Temperature



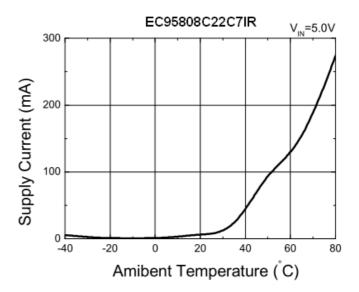
EC95808C22C7IR

(2) Supply Current v.s Input Voltage



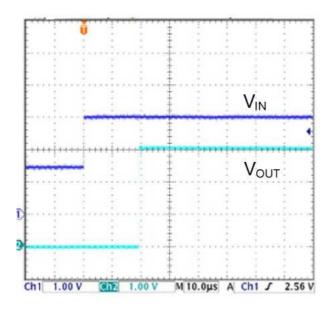
(4) Supply Current v.s Amibent

Temperature

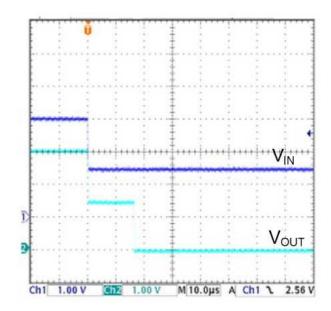




(5) Start-up Voltage Waveform



(6) Shutdown Voltage Waveform

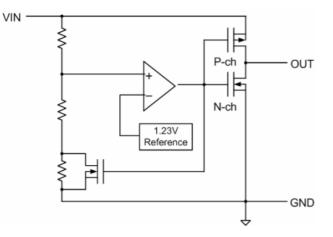




Detail Description

Basic Operation

For EC95808C CMOS Active low output:



(1) When the input voltage V_{IN} is higher than the release voltage V_{REL} ($V_{REL} = V_{DET} + V_{HYS}$), the N-ch MOS is OFF and P-ch MOS is ON to provide V_{IN} at the output. Since NMOS is OFF, the comparator input voltage is

V_{IN} x (R2+R3) / (R1+R2+R3)

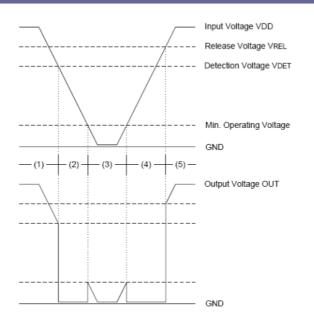
When the V_{IN} goes below the V_{REL} , V_{IN} keeps at the output since V_{IN} remains above the detection voltage V_{DET} . The difference between V_{REL} and V_{DET} is the hysteresis range.

(2) When the V_{IN} goes below the V_{DET} , the N-ch MOS is ON and P-ch MOS is OFF to provide GND level at the output. At this time NMOS is ON, the comparator input voltage is

V_{IN} x R2 / (R1+R2)

- (3) When the V_{IN} falls below the minimum opera-ting voltage, the output becomes undefined changed to V_{IN} if the output is pulled up to V_{IN}.
- (4) When the V_{IN} rises above the minimum opera-ting voltage, the GND level appears at the output. The GND level keeps at the output even when V_{IN} goes above the detection voltage V_{DET} , as long as it doesn't exceed the release voltage V_{REL} .



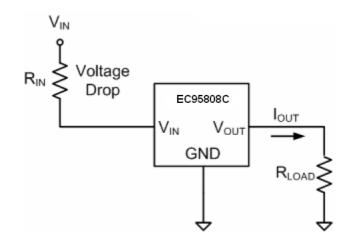


(5) When the V_{IN} rises above the release voltage V_{REL} , the N-ch MOS is OFF and P-ch MOS is ON to provide V_{IN} at the output.

Oscillation Notice

When a resistor is connected between the input voltage and the input pin V_{IN} with CMOS output configuration, oscillation may occur due to voltage drop at R_{IN} . The voltage drop is

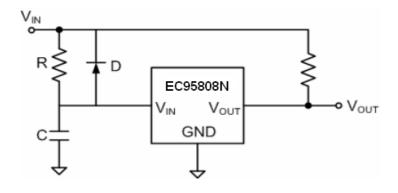
 $V_{DROP} = R_{IN} \times I_{OUT}$



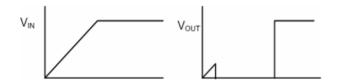
When the V_{IN} input voltage rises above the release voltage, the detector output voltage increases and the load current I_{OUT} will flow at R_{LOAD} . A voltage drop is produced at R_{IN} . The voltage drop will also lead to a fall in the input voltage at V_{IN} pin. When the V_{IN} input voltage falls below the detection voltage, output voltage falls to GND and the output current will cease. Then the voltage drop at R_{IN} will disappear, and the V_{IN} input voltage will rise to commence release operation. Oscillation may occur with this release detection-release repetition. It's recommended not to use the CMOS configuration when a resistor R_{IN} is connected between V_{IN} input pin and the power source. Please use N-channel open drain configuration when R_{IN} is required.



Power-on Reset Circuit

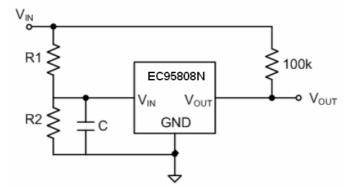


A power-on reset circuit example using EC95808N is shown in the figure. Resistor R should be 75 k Ω or less to avoid oscillation. Diode D instantaneously discharges the charge stored in the capacitor C at the power falling. Diode D can be removed when the delay of the falling time is not important.



Change of Detection Voltage

For EC95808N N-channel open drain output configuration, the detection voltage can be changed with resistance dividers as shown in the figure.



Detection voltage is changed to

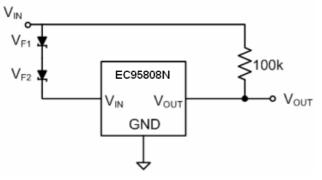
V_{DET} x (R1+R2) / R2

Hysteresis width is also changed to\

V_{HYS} x (R1+R2) / R2

Resistor R1 should be 75 k Ω or less to avoid oscillation. The detection voltage can also be changed with diodes as shown in the figure.



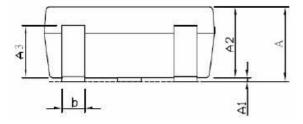


Detection voltage becomes

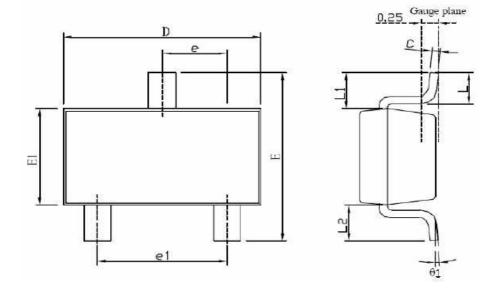
 V_{F1} + V_{F2} + V_{DET}

Mechanical Dimensions

OUTLINE DRAWING SOT23-3L



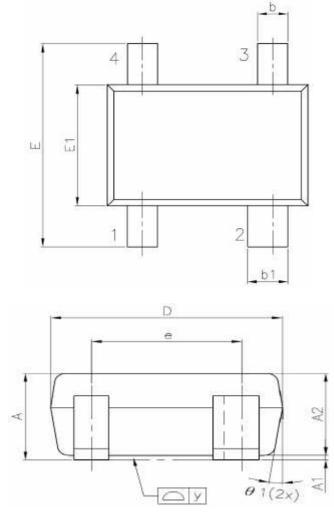
Sumbolo	Dimensions in Millmeters					
Symbols	Min	Nom	Max			
A	1.00	1.10	1.40			
A1	0.00	0.05	0.10			
A2	1.00	1.10	1.30			
A3	0.70	0.80	0.90			
b	0.35	0.40	0.50			
С	0.12	0.125	0.225			
D	2.70	2.90	3.10			
E	2.60	2.80	3.00			
E1	1.40	1.60	1.80			
e		0.95(Typ)	6			
e1	1000	1.90(Typ)	1000			
61	1°	5°	9°			
L	0.37					
L1		0.6REF				
L1-L2	100		0.12			





Mechanical Dimensions

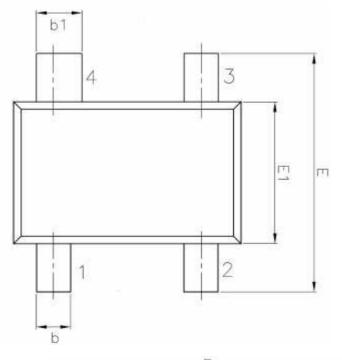
OUTLINE DRAWING SC82-4L(Pin Type I)

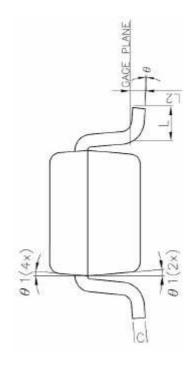


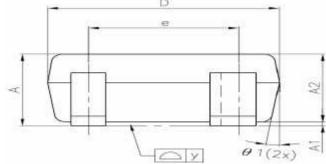
Complete la	Dimens	sion in mill	imeters	Dime	nsion in in	ches
Symbols	Min	Nom	Max	Min	Nom	Max
A	0.80	1.7.7.7.1	1.10	0.031	1	0.043
A1	0.00		0.10	0.000		0.004
A2	0.70	0.90	1.00	0.027	0.035	0.039
b	0.25	0.30	0.40	0.010	0.012	0.016
b1	0.35	0.40	0.50	0.014	0.016	0.020
с	0.10		0.26	0.004		0.010
D	1.80	2.00	2.20	0.071	0.079	0.087
E1	1.15	1.25	1.35	0.045	0.049	0.053
E	1.80	2.10	2.40	0.071	0.083	0.094
e		1.30			0.051	
L	0.26	0.36	0.46	0.010	0.014	0.018
L2		0.15		1.222	0.006	
У	3025		0.10			0.004
θ	0*	10000	8°	0°	(77772)	8*
01	4°	(12	4		12°



Mechanical Dimensions OUTLINE DRAWING SC82-4L(Pin Type S)

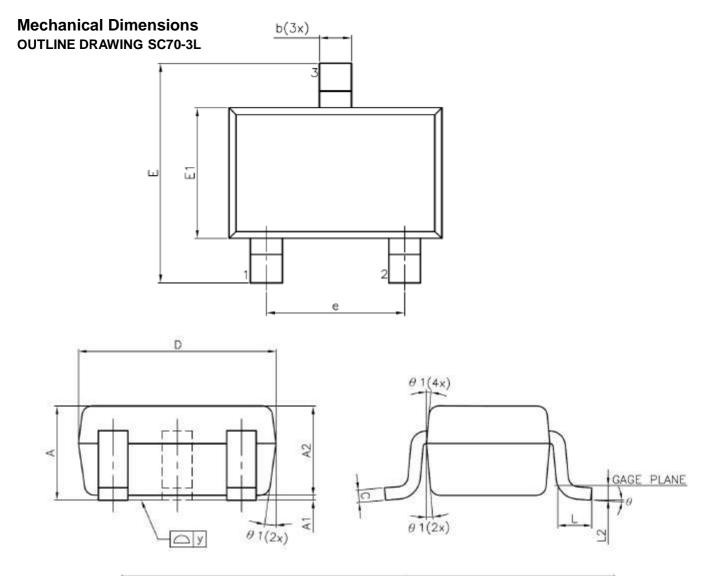






Cumbola	Dimension in millimeters			Dime	nsion in in	ches
Symbols	Min	Nom	Max	Min	Nom	Max
A	0.80		1.10	0.031		0.043
A1	0.00	(1 	0.10	0.000		0.004
A2	0.70	0.90	1.00	0.027	0.035	0.039
b	0.25	0.30	0.40	0.010	0.012	0.016
b1	0.35	0.40	0.50	0.014	0.016	0.020
с	0.10		0.26	0.004		0.010
D	1.80	2.00	2.20	0.071	0.079	0.087
E1	1.15	1.25	1.35	0.045	0.049	0.053
E	1.80	2.10	2.40	0.071	0.083	0.094
e		1.30			0.051	
L	0.26	0.36	0.46	0.010	0.014	0.018
L2	2000	0.15			0.006	
У	2020		0.10	1203		0.004
θ	0*		8	0°		8°
81	4°	(12"	4		12°





Countralia	Dimens	ions in mil	Imeters	Dimens	ions in mil	Imeters
Symbols	Min	Nom	Max	Min	Nom	Max
Α	0.80		1.10	0.031	: 	0.043
A1	0.00		0.10	0.000		0.004
A2	0.70	0.90	1.00	0.028	0.035	0.039
b	0.25	1000	0.40	0.010		0.016
С	0.08		0.22	0.003		0.009
D	1.80	2.00	2.20	0.071	0.079	0.087
E	1.80	2.10	2.40	0.071	0.083	0.094
E1	1.15	1.25	1.35	0.045	0.049	0.053
e	S	1.30			0.051	(100)
L	0.26	0.36	0.46	0.010	0.014	0.018
L2		0.15	2.25		0.006	
у	83775		0.10	027		0.004
θ	0°	4°	8 °	0°	4°	8°
01	4°		12°	4°	1	12°